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## Erratum: Leakage current measurements of a pixelated polycrystalline CVD diamond detector

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It has become necessary to write an erratum for this article as it conveyed the impression that the material under test was a standard polycrystalline diamond material. In fact, the material is a CVD diamond film grown by heteroepitaxy on iridium substrates which is known to have a crystal structure completely different from polycrystalline diamond films grown by other CVD techniques. Heteroepitaxy on iridium can produce material approaching the quality exhibited by single crystal material [1]. The crystal quality was not characterised in this paper as the sample measured was produced as a test sample for development of metallisation techniques and never foreseen for characterisation as a detector.

Due to the large band gap of the material and the extremely low leakage currents measured it is very difficult to draw any conclusions about the quality of the material and the comparison with the performance of polycrystalline material in the paper should not have been made. Indeed, the lack of any measureable polarisation effects over an applied bias range of +/-1000 V indicates that the material contains significantly lower numbers of the defects and grain boundaries that characterise polycrystalline material.

## References

[1] C. Stehl et al., Efficiency of dislocation density reduction during heteroepitaxial growth of diamond for detector applications, Appl. Phys. Lett. 103 (2013) 151905.

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